

FORM PTO-1449 US DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		Atty. Docket No. 80236DPCW Customer No. 01333		Serial No. To Be Assigned	
If AFTER the later date of the first Office Action or 3 months from filing, use only with Rule 97(E) Certificate or Fee		Applicant: Ramanathan Srinivasan, et al			
LIST OF ART CITED BY APPLICANT <i>(Use several sheets if necessary)</i>		Filing Date Herewith		Group To Be Assigned	

U.S. PATENT DOCUMENTS						
Examiner Initial*	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
<i>W</i>	5,738,800	14Apr1998	Hosali et al.	216	99	
<i>W</i>	5,759,917	02Jun1998	Grover et al.	438	690	
<i>W</i>	6,299,659 B1	09Oct2001	Kido et al.	51	309	
<i>W</i>	6,042,741	28Mar2000	Hosali et al.	252	79.1	
<i>W</i>	6,132,637	17Oct2000	Hosali et al.	252	79.1	
<i>W</i>	6,218,305 B1	17Apr2001	Hosali et al.	438	691	
<i>W</i>	6,027,554	22Feb2000	Kodama et al.	106	3	
<i>W</i>	5,876,490	02Mar1999	Ronay	106	3	
<i>W</i>	5,575,885	19Nov1996	Hirabayashi et al.	156	626.1	
<i>W</i>	5,733,819	31Mar1998	Kodama et al.	438	692	
<i>W</i>	6,410,444	25Jun2002	Kido et al.	438	693	
<i>W</i>	6,436,835	20Aug2002	Kido et al.	438	693	

FOREIGN PATENT DOCUMENTS						
Examiner Initial*	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO
<i>W</i>	WO99/43761	01Sep1999	PCT (See EP1061111A1 for english equivalent)			X
<i>W</i>	EP 1 061 111 A1	20Dec2000	EPO (Eng. Eqv. WO99/43761)			X
<i>W</i>	0 786 504 A2	30Jul1997	EP	C09G	1/02	X
<i>W</i>	0 846 740 A1	10Jun1998	EP	C09G	1/02	X
<i>W</i>	0 853 335 A2	15Jul1998	EP	H01L	21/3105	X
<i>W</i>	WO 99/53532	21Oct1999	PCT	H01L	21/00	X
<i>W</i>	0 659 858 A2	28Jun1995	EP	C09G	1/02	X

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)	
<i>W</i>	Chemical Mechanical Planarization of Microelectronic Materials, "8.1.2 Shallow Trench Isolation"; by J. M. Steigerwald, S. P. Muraka, and R. J. Gutman; ISBN 0-471-13827-4 (Jon Wiley & Son, Inc. 1997), pages 273-274.
<i>W</i>	A High Oxide/Nitride Selectivity CMP Slurry For Shallow Trench Isolation; by Sharath Hosali and Ray Lavoie; Electrochemical Society Proceedings, Volume 98-7, pages 218-234.
<i>W</i>	Application of Ceria-Based High Selectivity Slurry to STI CMP for Sub 0.18 μm CMOS Technologies; by Ki-Sik Choi, Sang-Ick Lee, Chang-Il Kim, Chul-Woo Nam, Sam-Dong Kim, and Chung-Tae Kim; CMP-MIC Conference, February 11-12, 1999, pages 307-313.
<i>W</i>	A Production-Proven Shallow Trench Isolation (STI) Solution Using Novel CMP Concepts; by Raymond R. Jin, Jeffery David, Bob Abbassi, Tom Osterheld, and Fritz Redeker; CMP-MIC Conference, February 11-12, 1999, pages 314-321.
<i>W</i>	A Wide Margin CMP and Clean Process For Shallow Trench Isolation Applications; by Brad Withers, Eugene Zhao, Rahul Jairath; CMP-MIC Conference, February 19-20, 1998, pages 319-327.
<i>W</i>	Planarization Process and Consumable Development For Shallow Trench Isolation; by Sharath D. Hosali, et al.; CMP-MIC Conference, February 13-14, 1997, pages 52-57.
<i>W</i>	Pattern Dependence And Planarization Using Silica Or Ceria Slurries For Shallow Trench Isolation; by D. R. Evans, et al.; CMP-MIC Conference, February 19-20, 1998, pages 347-350.
<i>W</i>	A Two-Step CMP-RIE Planarization Sequence For Advanced Trench Isolation Process; by Konstantin Smekalin; CMP-MIC Conference, February 13-14, 1997, pages 21-28.
<i>W</i>	Raising Oxide/Nitride Selectivity To Aid In The CMP Of Shallow Trench Isolation Type Applications; by C.R. Mills, et al.; CMP-MIC Conference, February 13-14, 1997, pages 179-185.

EXAMINER 	DATE CONSIDERED 9/8/05
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* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.